1A 4Quadrants TRIAC

Product Summary

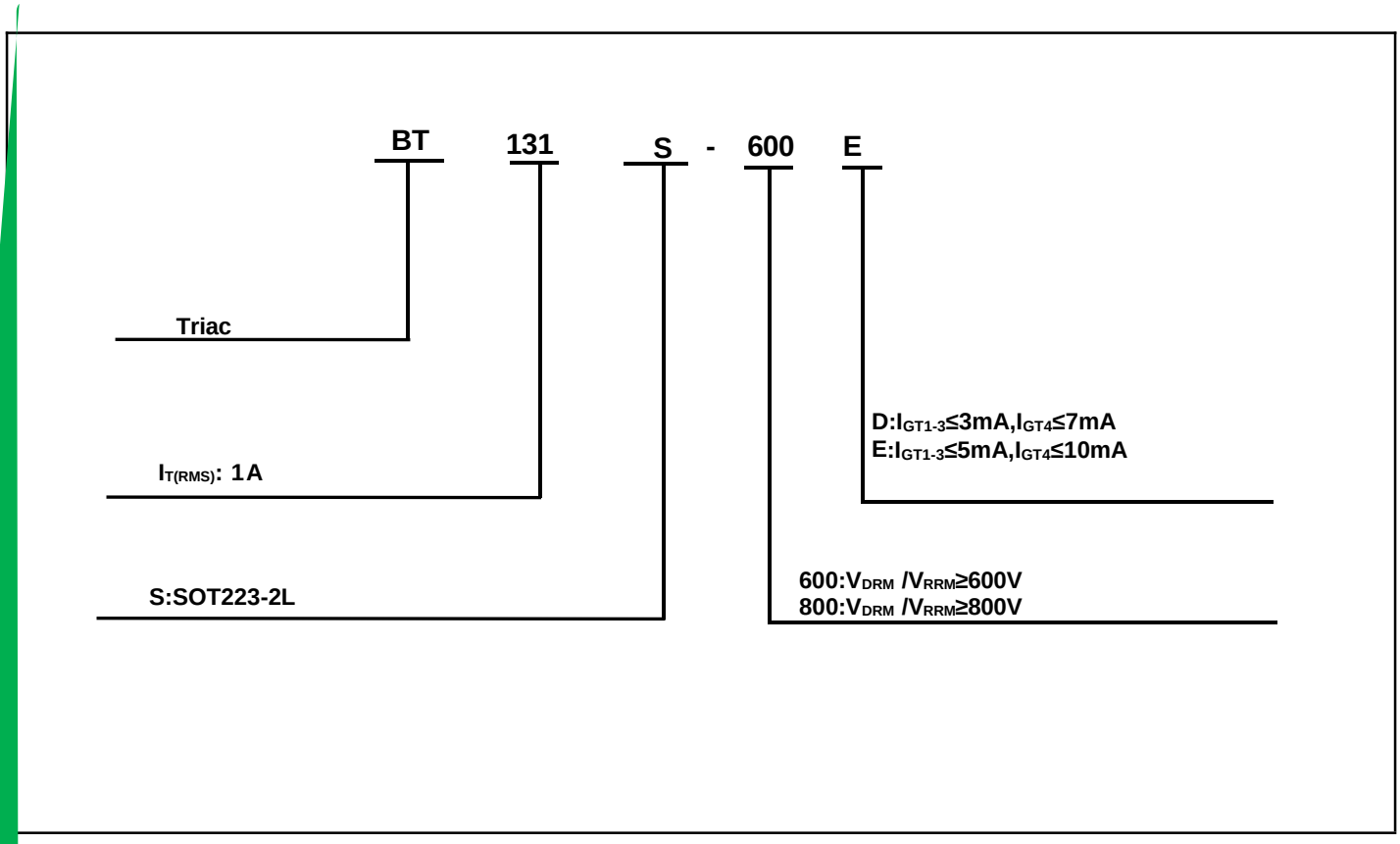
Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM} V_{RRM}	600/800	V
V_{TM}	1.55	V

FEATURES

- NPNPN five-layer structure silicon bidirectional device
- P-type counter-diffusion isolation
- Mesa glass passivation process
- Multi-layer metal back electrode
- RoHS compliant

APPLICATIONS

- Heat


BT
131
S
-
600
E
Triac
IT(RMS): 1A
S:SOT223-2L
D:IGT1-3≤3mA,IGT4≤7mA
E:IGT1-3≤5mA,IGT4≤10mA
600:VDRM /VRRM≥600V
800:VDRM /VRRM≥800V

Typical Characteristic

Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
	Tape/Reel,7”reel	1000pcs/Reel	6000PCS/Box 30000PCS/Carton
	Tape/Reel,13”reel	2500pcs/Reel	5000PCS/Box 30000PCS/Carton

1.2mm

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